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(71) Applicant (for all designated States except US): **AGENCY FOR SCIENCE, TECHNOLOGY AND RESEARCH** [SG/SG]; 1 Fusionopolis Way, #20-10 Connexis, Singapore 138632 (SG).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **NG, Sum Huan** [SG/SG]; Block 638C, Punggol Drive, #14-463, Singapore 823638 (SG). **WANG, Zhenfeng** [SG/SG]; Block 412, Jurong West Street 42, #04-857, Singapore 640412 (SG).

(74) Agent: **ATMD BIRD & BIRD LLP**; 39 Robinson Road #07-01, Robinson Point, Singapore 068911 (SG).

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(54) Title: METHOD OF MAKING A MULTILAYER SUBSTRATE WITH EMBEDDED METALLIZATION

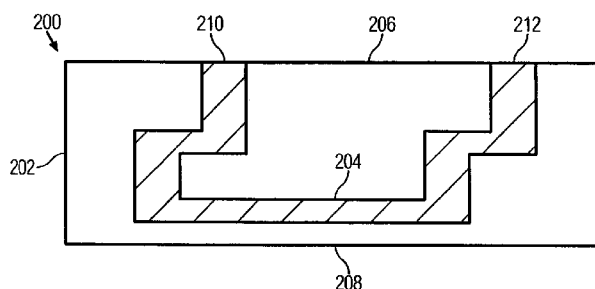


FIG. 3

(57) Abstract: A method of making a substrate includes providing an upper insulative layer and a lower insulative layer, wherein the upper insulative layer includes an inlet opening, the lower insulative layer includes a channel, and the inlet opening is in fluid communication with the channel, flowing a non-solidified material through the inlet opening into the channel, and then solidifying the non-solidified material by applying energy to the non-solidified material, thereby forming embedded metallization in the channel. The substrate can be a microfluidic device, an electrical interconnect or other electronic devices.

